Product Preview

Low-Voltage CMOS Octal Buffer Flow Through Pinout

With 5 V-Tolerant Inputs and Outputs (3-State, Inverting)

The 74LVC540A is a high performance, inverting octal buffer operating from a 1.2 to 3.6 V supply. This device is similar in function to the MC74LCX240, while providing flow through architecture. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows 74LVC540A inputs to be safely driven from 5 V devices. The 74LVC540A is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable $(\overline{OE1}, \overline{OE2})$ inputs, when HIGH, disables the outputs by placing them in a HIGH Z condition.

Features

- Designed for 1.2 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- \bullet I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0~V$
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 250 mA
- ESD Performance:
 - ♦ Human Body Model > 2000 V
 - ♦ Machine Model > 200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



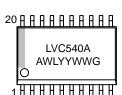
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MARKING DIAGRAMS

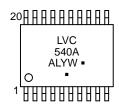


SOIC-20 WB DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

L, WL = Wafer Lot

Y, YY = Year

W, WW = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

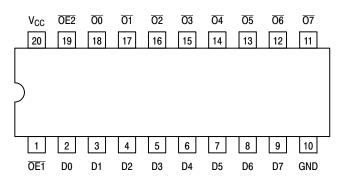


Figure 1. Pinout: 20-Lead (Top View)

PIN NAMES

Pins	Function
OEn	Output Enable Inputs
Dn	Data Inputs
On	3-State Outputs

TRUTH TABLE

Inputs			Outputs	
OE1	OE2	Dn	On	
L	L	L	Н	
L	L	Н	L	
Х	Н	Х	Z	
Н	Х	Х	Z	

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

 $X = High \ or \ Low \ Voltage \ Level \ and \ Transitions \ are \ Acceptable For I_{CC} \ reasons, \ DO \ NOT \ FLOAT \ Inputs$

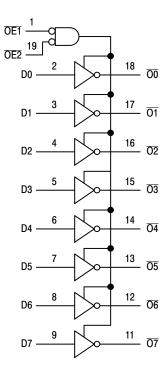


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +6.5$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +6.5$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	T _L = 260		°C
TJ	Junction Temperature Under Bias	T _J = 135		°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC = 65.8 TSSOP = 110.7		°C/W
MSL	Moisture Sensitivity		Level 1	
I _{LATCHUP}	Latch-up Performance at V _{CC} = 3.6 V and 125°C (Note 3)		±250	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- 3. Tested to EIA/JES078.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3-State	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			-24 -12	mA
I _{OL}	LOW Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$			24 12	mA
T _A	Operating Free–Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			-40°C to +85°C		-40	°C to +12	5°C		
Symbol	Parameter	Conditions	Min	Typ (Note 4)	Max	Min	Typ (Note 4)	Max	Unit
VIH	HIGH-level input	V _{CC} = 1.2 V	1.08	-	-	1.08	-	-	V
	voltage	V _{CC} = 1.65 V to 1.95 V	0.65 x V _{CC}	_	_	0.65 x V _{CC}	-	-	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	-	-	1.7	_	ı	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	_	-	2.0	_	-	
V_{IL}	LOW-level input	V _{CC} = 1.2 V	-	_	0.12	-	-	0.12	V
	voltage	V _{CC} = 1.65 V to 1.95 V	-	_	0.35 x V _{CC}	-	-	0.35 x V _{CC}	
		V _{CC} = 2.3 V to 2.7 V	-	_	0.7	-	-	0.7	
		V _{CC} = 2.7 V to 3.6 V	-	_	0.8	-	-	8.0	
V _{OH}	HIGH-level output	$V_I = V_{IH}$	or V _{IL}						V
	voltage	$I_O = -100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	V _{CC} – 0.2	-	-	V _{CC} - 0.3	-	_	
		$I_O = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	_	-	1.05	-	-	
		$I_O = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	-	
		$I_O = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	_	-	2.05	-	-	
		$I_O = -18 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	_	-	2.25	-	-	
		$I_O = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.2	_	-	2.0	-	-	
VOL	LOW-level output	$V_I = V_{IH}$	or V _{IL}						V
	voltage	$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	-	_	0.2	-	-	0.3	
		I _O = 4 mA; V _{CC} = 1.65 V	-	_	0.45	_	_	0.65	
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	_	0.6	_	_	0.8	
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	-	_	0.6	
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	ı	-	0.55	-	_	0.8	
I _I	Input leakage current	$V_I = 5.5 \text{V}$ or GND $V_{CC} = 3.6 \text{ V}$	-	±0.1	±5	-	±0.1	±20	μΑ
l _{OZ}	OFF-state output current	VI = VIH or VIL; $V_O = 5.5 \text{ V or GND}; V_{CC} = 3.6 \text{ V}$	-	±0.1	±5	-	±0.1	±20	μΑ
I _{OFF}	Power-off leakage current	$V_1 \text{ or } V_0 = 5.5 \text{ V}; V_{CC} = 0.0 \text{ V}$	ı	±0.1	±10	-	±0.1	±20	μΑ
I _{CC}	Supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6 \text{ V}$	1	0.1	10	-	0.1	40	μΑ
ΔI_{CC}	Additional supply current	per input pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.7 V to 3.6 V	-	5	500	_	5	5000	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. All typical values are measured at $T_A = 25^{\circ}C$ and $V_{CC} = 3.3$ V, unless stated otherwise.

AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}$)

			-40	°C to +8	5°C	-40°	°C to +12	25°C	
Symbol	Parameter	Conditions	Min	Typ ⁵	Max	Min	Typ ⁵	Max	Unit
t _{pd}	Propagation Delay (Note 6)	V _{CC} = 1.2 V	-	18.0	-	-	_	-	ns
	INDIT to NOT	V _{CC} = 1.65 V to 1.95 V	1.0	-	16.4	1.0	_	16.4	
		V _{CC} = 2.3 V to 2.7 V	1.0	-	7.8	1.0	_	7.8	
		V _{CC} = 2.7 V	1.0	-	7.1	1.0	_	7.1	
		V _{CC} = 3.0 V to 3.6 V	1.0	-	5.3	1.0	_	5.3	
t _{en}	Enable Time (Note 7)	V _{CC} = 1.2 V	-	20.0	_	-	_	-	ns
	nOE to nOn	V _{CC} = 1.65 V to 1.95 V	1.0	-	16.5	1.0	_	16.5	
		V _{CC} = 2.3 V to 2.7 V	1.0	-	10.5	1.0	_	10.5	
		V _{CC} = 2.7 V	1.0	-	8.0	1.0	_	8.0	
		V _{CC} = 3.0 V to 3.6 V	1.0	-	6.6	1.0	_	6.6	
t _{dis}	Disable Time (Note 8)	V _{CC} = 1.2 V	-	18.0	_	-	_	-	ns
	INOE to NON	V _{CC} = 1.65 V to 1.95 V	1.0	-	15.9	1.0	_	15.9	
		V _{CC} = 2.3 V to 2.7 V	1.0	-	9.0	1.0	-	9.0	
		V _{CC} = 2.7 V	1.0	-	8.2	1.0	_	8.2	
		V _{CC} = 3.0 V to 3.6 V	1.0	-	7.4	1.0	_	7.4	
t _{sk(0)}	Output Skew Time (Note 9)		-	_	1.0	-	_	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 5. Typical values are measured at TA = 25°C and Vcc = 3.3 V, unless stated otherwise.
- 6. t_{pd} is the same as t_{PLH} and t_{PHL}.
- 7. t_{en} is the same as t_{PZL} and t_{PZH}.
- 8. t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- 9. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 10)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 10)	$\begin{aligned} &V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ &V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

^{10.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

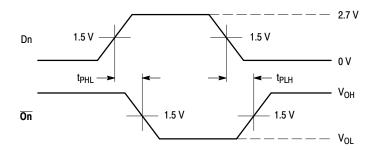
Symbol	Parameter	Condition	Typical	Unit	
CIN	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	5.0	pF	
Соит	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	7.0	pF	
C_{PD}	Power Dissipation Capacitance	Per input; V _I = GND or V _{CC}			
	(Note 11)	V _{CC} = 1.65 V to 1.95 V	7.7		
		V _{CC} = 2.3 V to 2.7 V	11.3		
		V _{CC} = 3.0 V to 3.6 V	14.4		

^{11.} C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

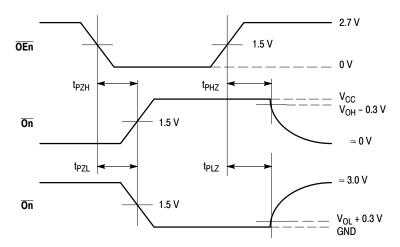
 $P_D = C_{PD} * V_{CC}^2 x fi * N + \Sigma (C_L x V_{CC}^2 x fo)$ where: fi = input frequency in MHz; fo = output frequency in MHz

 C_L = output load capacitance in pF V_{CC} = supply voltage in Volts

N = number of outputs switching $\Sigma(C_L * V_{CC}^2 x \text{ fo})$ = sum of the outputs.



WAVEFORM 1 – PROPAGATION DELAYS $t_R = t_F = 2.5~\text{ns},\,10\%$ to 90%; f = 1 MHz; $t_W = 500~\text{ns}$

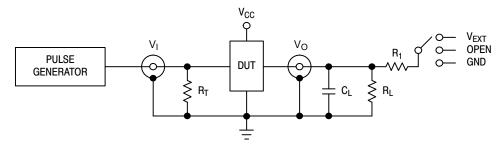


WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 t_{R} = t_{F} = 2.5 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

Figure 3. AC Waveforms

	V _{CC}						
Symbol	3.3 V \pm 0.3 V	2.7 V	V _{CC} < 2.7 V				
Vmi	1.5 V	1.5 V	V _{CC} /2				
Vmo	1.5 V	1.5 V	V _{CC} /2				
V_{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V				
V _{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V				



 C_L includes jig and probe capacitance R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$ R_1 = R_L

Supply Voltage	Input		Load V _{EXT}		Load		
V _{CC} (V)	VI	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
1.65 – 1.95	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
2.3 – 2.7	V _{CC}	≤ 2 ns	30 pF	500 Ω	Open	2 x V _{CC}	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V _{CC}	GND
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V _{CC}	GND

Figure 4. Test Circuit

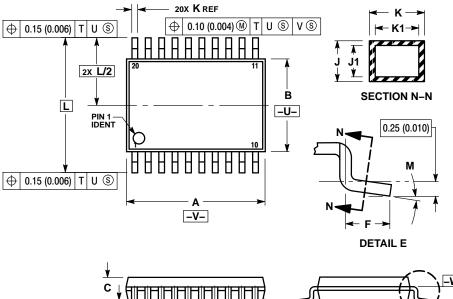
ORDERING INFORMATION

Device	Package	Shipping [†]
74LVC540ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
74LVC540ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**

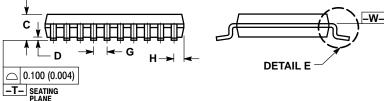


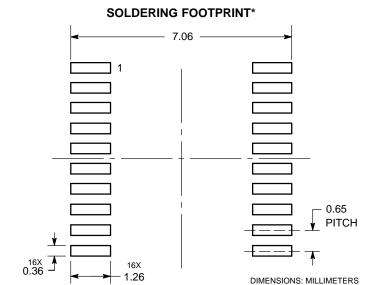
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

- MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
- CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

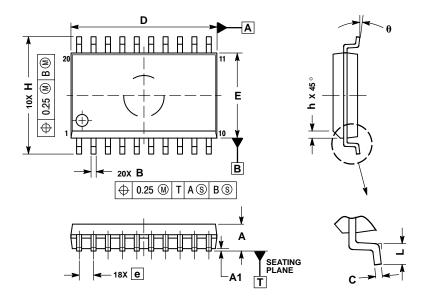




*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-20 WB CASE 751D-05 ISSUE G



NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
Α	2.35	2.65
A1	0.10	0.25
В	0.35	0.49
С	0.23	0.32
D	12.65	12.95
Е	7.40	7.60
е	1.27 BSC	
Н	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

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